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Invention: METHOD FOR MANUFACTURING COMPOUND SEMICONDUCTOR  
EPITAXIAL SUBSTRATE

Inventor: Kenji KOHIRO  
Tomoyuki TAKADA

**CUSTOMER NO. 42798**

Fitch, Even, Tabin & Flannery  
1801 K Street, N.W. - Suite 401L  
Washington, D.C. 20006-1201  
Telephone: (202) 419-7000

This is a:

- ☐ Provisional Application
- ☐ Regular Utility Application
- ☐ Divisional Application
- ☒ PCT National Phase Application
  - The complete disclosure of  
PCT/JP2004/016905, filed November 8,  
2004 is incorporated by reference.
- ☐ Design Application
- ☐ Reissue Application
- ☐ Plant Application
- ☐ Substitute Specification
- ☐ Sub. Spec. Filed \_\_\_\_\_  
In Appl. No. \_\_\_\_/\_\_\_\_
- ☐ Marked-up Specification re  
Sub. Spec. filed \_\_\_\_\_  
In Appl. No. \_\_\_\_/\_\_\_\_

**SPECIFICATION**

DESCRIPTION

METHOD FOR MANUFACTURING COMPOUND SEMICONDUCTOR EPITAXIAL

5 SUBSTRATE

TECHNICAL FIELD

The present invention relates to a method for manufacturing a compound semiconductor epitaxial substrate.

10 More specifically, the invention relates to a method for manufacturing a compound semiconductor epitaxial substrate with few concave defects.

BACKGROUND ART

15 When an epitaxial layer has been grown on a single crystal substrate by conventional vapor phase epitaxy, in particular, metal-organic chemical vapor deposition (MOCVD), convex defects or concave defects have sometimes generated on or in a surface of the epitaxial layer.

20 Convex defects are called tear-drop-like defects or hillocks; their diameters are 10  $\mu\text{m}$  to 30  $\mu\text{m}$  and their heights are several tens of nanometers. Despite the convex defects, semiconductor devices can be manufactured, but in some cases, the defects have damaged photo masks used in their

25 manufacturing process or have caused displacements of

patterns. Therefore, to reduce convex defects, a method of controlling off-angle of single crystal substrate have been proposed (for example, JP-A-2-239188 and JP-A-8-78348).

On the other hand, concave defects have diameters of several micrometers and depth reaching the vicinity of an interface between a single crystal substrate and an epitaxial layer. When a semiconductor device is manufactured by using a compound semiconductor epitaxial substrate with concave defects, the semiconductor device yield decreases.

Besides, it has been difficult to reduce the concave defects through the use of the method for reducing the convex defects.

#### DISCLOSURE OF THE INVENTION

An object of the present invention is to provide a method for manufacturing a compound semiconductor epitaxial substrate with few concave defects.

The present inventors conducted extensive studies to reduce the concave defects, and resultantly completed the invention.

That is, the present invention provides a method for manufacturing a compound semiconductor epitaxial substrate comprising a step of epitaxially growing an InGaAs layer on an InP single crystal substrate or on an epitaxial layer lattice-matched to the InP single crystal substrate under

conditions of

ratio of V/III: 10-100,

growth temperature: 630°C-700°C and

growth rate: 0.6 µm/h - 2 µm/h.

5 Further, the present invention provides a method for reducing concave defects in a compound semiconductor epitaxial substrate comprising a step of epitaxially growing an InGaAs layer on an InP single crystal substrate or on an epitaxial layer lattice-matched to the InP single crystal  
10 substrate under conditions of

ratio of V/III: 10-100,

growth temperature: 630°C-700°C and

growth rate: 0.6 µm/h - 2 µm/h.

Furthermore, the present invention provides a compound  
15 semiconductor epitaxial substrate obtained by using the above manufacturing method.

#### EFFECT OF THE INVENTION

According to the method for manufacturing a compound  
20 semiconductor epitaxial substrate of the present invention, a compound semiconductor epitaxial substrate with few concave defects is obtained.

Also, according to the method of the present invention, it is possible to reduce concave defects in a compound  
25 semiconductor epitaxial substrate.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 shows a cross-sectional view of a compound semiconductor epitaxial substrate obtained by using the manufacturing method according to the present invention.

Fig. 2 shows a cross-sectional view of a compound semiconductor epitaxial substrate obtained in Example 1.

Fig. 3 is a photograph of a surface of the compound semiconductor epitaxial substrate obtained in Example 1.

Fig. 4 shows an indium distribution within an InGaAs layer included in the compound semiconductor epitaxial substrate obtained in Example 1.

Fig. 5 shows an indium distribution within an InGaAs layer included in a compound semiconductor epitaxial substrate obtained in Example 2.

Fig. 6 is a photograph of a surface of a compound semiconductor epitaxial substrate obtained in Comparative example 2.

Fig. 7 shows a relationship between growth temperature of InGaAs layer and surface defect density of compound semiconductor epitaxial substrate obtained.

Fig. 8 shows a relationship between growth rate of InGaAs layer and surface defect density of compound semiconductor epitaxial substrate obtained.

Fig. 9 shows a relationship between V/III ratio of grown

InGaAs layer and surface defect density of compound semiconductor epitaxial substrate obtained.

BEST MODE FOR CARRYING OUT THE INVENTION

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**METHOD FOR MANUFACTURING COMPOUND SEMICONDUCTOR EPITAXIAL SUBSTRATE**

A method for manufacturing a compound semiconductor epitaxial substrate according to the present invention is  
10 illustrated with reference to Fig. 1. Fig. 1 is a cross-sectional view of a compound semiconductor epitaxial substrate (hereinafter abbreviated as "epitaxial substrate") 1 obtained by using the above manufacturing method. The epitaxial substrate 1 includes an InP substrate  
15 2, an optional InP layer 3, an InGaAs layer 4, and an optional InP layer 5 in this order.

The InP substrate 2 is, for example, a single crystal substrate with an off-angle, which is a deviation from a plane direction (100), of about not more than 5°, preferably not  
20 more than 0.5°. The InP substrate 2 is preferably a substrate with an off-angle of about 0° (just substrate) in viewpoint of controlling the amount of impurities entrapped into the epitaxial layer and of applications in semiconductor lasers. Further, The InP substrate 2 has preferably the plane  
25 direction accuracy of  $\pm 0.05^\circ$  in the (100).

A layer (for example, the InP layer 3 shown in Fig. 1) being lattice-matched to the InP substrate 2 is preferably grown on the InP substrate 2. Examples of the epitaxial layer  
 5 being lattice-matched to the InP substrate 2 include an InP layer, InGaAs layer, InAlAs layer, InGaAsP layer, and GaAsSb layer. The layer being lattice-matched to the InP substrate 2 may be grown by vapor growth such as MOCVD and molecular beam epitaxy (hereinafter referred to as MBE). The vapor  
 10 growth of the InP substrate 2 may be carried out under conventional conditions.

The InGaAs layer 4 is grown on the InP substrate 2, or on an optional epitaxial layer grown on InP substrate 2 which  
 15 is lattice-matched to the InP substrate 2. The InGaAs layer 4 may be grown by vapor growth such as MOCVD and MBE, preferably grown by MOCVD.

The ratio of V/III in the vapor growth of the InGaAs layer 4 is not less than 10, preferably not less than 50 and is not  
 20 more than 100, preferably not more than 70. When the ratio of V/III is within the above range, an epitaxial substrate with few concave defects is obtained. When the ratio of V/III is lower than 10, group V vacancy defects generate in the epitaxial layer or anti-site defects (phenomena in which the  
 25 group III elements occupy group V sites) generate. It is

assumed that the group V vacancy defect is related to shortage of the group V elements. The ratio of V/Ⅲ means a proportion of feed rate of group V raw material to feed rate of group Ⅲ raw material for the manufacture of the Ⅲ-V group epitaxial  
5 substrate. For example, in vapor growth, an organic metal used as a raw material is fed in gaseous form from a gas cylinder or a bubbler.

When the gas cylinder is used, a feed rate of a raw material gas may be controlled by using a flow controller such  
10 as a MASSFLOW placed on a feed line. The feed rate of raw material gas is represented as "concentration of raw material gas in the gas cylinder" × "flow rate of raw material gas".

When the bubbler is used, the feed rate of the raw material gas may be controlled by using a flow controller such  
15 as a MASSFLOW placed on a feed which supplies a carrier gas to the bubbler. The feed rate of raw material gas is represented as "flow rate of carrier gas" × "vapor pressure of raw material in bubbler" / "gas pressure in the bubbler".

Examples of the group V raw material include arsine  
20 ( $\text{AsH}_3$ ). Examples of the group Ⅲ raw material include indium compounds such as trimethyl indium (TMIn), gallium compounds such as trimethyl gallium (TMGa) and triethyl gallium (TEGa). The gallium compound is preferably TMGa. By using TMGa, an epitaxial substrate including an epitaxial layer with uniform  
25 distribution of indium (In) is obtained.



A vapor growth temperature of the InGaAs layer 4 is not less than 630°C, preferably not less than 640°C, more preferably not less than 650°C and not more than 700°C, preferably not more than 680°C, more preferably not more than 670°C. When the vapor growth temperature is within the above range, an epitaxial substrate with few concave defects is obtained.

A vapor growth rate of the InGaAs layer 4 is not less than 0.6 µm/h, preferably not less than 0.8 µm/h and not more than 2 µm/h, preferably not more than 1.2 µm/h. The vapor growth rate may be controlled by adjusting the feed rate of raw material gas.

In the method for manufacturing a compound semiconductor epitaxial substrate according to the present invention, further, a layer may be further grown on the InGaAs layer 4. For example, a InP layer 5 may be grown thereon. The InP layer 5 may be grown by vapor growth such as MOCVD and MBE.

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#### **METHOD OF REDUCING CONCAVE DEFECTS IN COMPOUND SEMICONDUCTOR EPITAXIAL SUBSTRATE**

In the method of reducing concave defects in a compound semiconductor epitaxial substrate according to the present invention, the concave defects is reduced by growing an InGaAs

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layer on a single crystal InP substrate by vapor growth such as MOCVD and MBE under the same conditions as described above (ratio of V/III, temperature, growth rate, In raw material, Ga raw material and As raw material). The single crystal InP  
5 substrate may have an off-angle of about not more than 5°, preferably not more than 0.5°.

#### COMPOUND SEMICONDUCTOR EPITAXIAL SUBSTRATE

A compound semiconductor epitaxial substrate according  
10 to the present invention includes, for example, an InP substrate 2, an optional InP layer 3, an InGaAs layer 4, and an optional InP layer 5 in this order as shown in Fig. 1.

The InP substrate 2 has a thickness of not less than about 250  $\mu\text{m}$  and not more than about 700  $\mu\text{m}$ . In the epitaxial  
15 substrate including the InP layer 3, the InP layer 3 has a thickness of not less than about 0  $\mu\text{m}$  and not more than about 3  $\mu\text{m}$ . The InGaAs layer 4 has a thickness of not less than about 0.1  $\mu\text{m}$  and not more than about 6  $\mu\text{m}$  and an In content of not less than about 0.51, preferably not less than about  
20 0.52 and not more than about 0.53. Further, in the epitaxial substrate including the InP layer 5, the InP layer 5 has a thickness of not less than 0  $\mu\text{m}$  and not more than 2  $\mu\text{m}$ .

The compound semiconductor epitaxial substrate is obtained by using the above method for manufacturing a  
25 compound semiconductor epitaxial substrate.

### EXAMPLES

The following examples will illustrate the present invention more in detail, but do not limit the scope of the  
5 invention.

#### Example 1

A compound semiconductor epitaxial substrate 1' which has a layer structure shown in Fig. 2 and is used for the  
10 manufacture of a p-i-n diode, was obtained by using the following method.

An InP substrate 2', which is a just substrate with a plane direction (100) and has a plane direction accuracy within  $\pm 0.05^\circ$  and a diameter of about 8 cm, was placed in a  
15 MOCVD reactor for growing thin film.

The InP substrate 2' was surface-treated by elevating a temperature in the reactor to  $660^\circ\text{C}$  and feeding a  $\text{PH}_3$  gas. InP layer 3' having a thickness of  $1\ \mu\text{m}$  was grown on the InP substrate 2' using TMin as a raw material. Then the  $\text{PH}_3$  gas  
20 was changed for an  $\text{AsH}_3$  gas, an InGaAs layer 4' having a thickness of  $3\ \mu\text{m}$  was grown under conditions of

raw material : TMin and TEGa,  
ratio of V/III : 70,  
growth temperature :  $660^\circ\text{C}$ , and  
25 growth rate :  $1\ \mu\text{m/h}$ .

The AsH<sub>3</sub> gas was changed for the PH<sub>3</sub> gas, an InP layer 5' having a thickness of 1 μm was grown.

The epitaxial substrate had a good surface quality of the InP layer 5' and no concave defects on the surface. A photograph of the surface was shown in Fig. 3. The surface was observed by using a differential interference microscope. The In distribution in the InGaAs layer 4 of the epitaxial substrate obtained was shown in Fig. 4. In Fig. 4, a longitudinal axis indicated indium content(unit: %). The indium distribution was measured by using a high-resolution X-ray micro analyzer.

#### Example 2

An epitaxial substrate was obtained by the same operation as in Example 1 except that TEGa was changed for TMGa as the Ga raw material for growing the InGaAs layer 4.

The epitaxial substrate had a good surface quality and no concave defects on the surface. The indium distribution in the InGaAs layer 4 was shown in Fig. 5.

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#### Example 3

An epitaxial substrate was obtained by the same operation as in Example 2 except that the conditions for growing the InGaAs layer 4 was changed for the following.

25 ratio of V/III: 20,

growth temperature: 690° C, and

growth rate: 2  $\mu\text{m/h}$ .

The epitaxial substrate had a good surface quality and no concave defects on the surface.

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#### Comparative example 1

An epitaxial substrate was obtained by the same operation as in Example 1 except that the conditions for growing the InGaAs layer 4 was changed for the following.

10 ratio of V/III: 70,

growth temperature: 620° C, and

growth rate: 1  $\mu\text{m/h}$ .

The epitaxial substrate had no good surface quality and many concave defects on the surface.

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#### Comparative example 2

An epitaxial substrate was obtained by the same operation as in Example 1 except that the conditions for growing the InGaAs layer 4 was changed for the following.

20 ratio of V/III: 70,

growth temperature: 660° C, and

growth rate: 3  $\mu\text{m/h}$ .

The epitaxial substrate had no good surface quality and many concave defects on the surface. A photograph of the surface was shown in Fig. 6.

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### Comparative example 3

An epitaxial substrate was obtained by the same operation as in Example 2 except that the conditions for  
5 growing the InGaAs layer 4 was changed for the following.

ratio of V/III: 120,

growth temperature: 660°C, and

growth rate: 1  $\mu\text{m/h}$ .

The epitaxial substrate had no good surface quality and  
10 many concave defects on the surface.

### Test example 1

An InP substrate 2', which is a just substrate with a plane direction (100) and has a plane direction accuracy  
15 within  $\pm 0.05^\circ$  and a diameter of about 8 cm, was placed in a MOCVD reactor for growing thin film.

The InP substrate 2' was surface-treated by elevating a temperature in the reactor to 660°C and feeding a  $\text{PH}_3$  gas. InP layer 3' having a thickness of 1  $\mu\text{m}$  was grown on the InP  
20 substrate 2' using TMIIn as a raw material. Then the  $\text{PH}_3$  gas was changed for an  $\text{AsH}_3$  gas, an InGaAs layer 4' having a thickness of 3  $\mu\text{m}$  and indium content of 0.53 was grown under conditions of

raw material : TMIIn and TEGa,

25 ratio of V/III : 63.4,

growth temperature : 660-700°C, and

growth rate : 1  $\mu\text{m}/\text{h}$ .

The  $\text{AsH}_3$  gas was changed for the  $\text{PH}_3$  gas, an InP layer 5' having a thickness of 1  $\mu\text{m}$  was grown. On growth temperature within  
5 the above range, the operations were repeated to obtain several epitaxial substrates.

Concave defect densities on the surfaces (of the InP layers 5') of the epitaxial substrates were shown in Fig. 7. The concave defect densities were measured by using a surface  
10 defect analyzer(Surfscan 6220).

#### Test example 2

An epitaxial substrate was obtained by the same operation as in Test example 1 except that the conditions for  
15 growing the InGaAs layer 4 was changed for the following.

ratio of V/III: 63.4,

growth temperature: 650°C, and

growth rate: 0.5-3  $\mu\text{m}/\text{h}$ .

On growth rate within the above range, the operations were  
20 repeated to obtain several epitaxial substrates. Concave defect densities on the surfaces of the epitaxial substrates were shown in Fig. 8.

#### Test example 3

25 An epitaxial substrate was obtained by the same

operation as in Test example 1 except that the conditions for growing the InGaAs layer 4 was changed for the following.

ratio of V/III: 30-112,

growth temperature: 650°C, and

5 growth rate: 1  $\mu\text{m/h}$ .

On rate of V/III within the above range, the operations were repeated to obtain several epitaxial substrates. Concave defect densities on the surfaces of the epitaxial substrates were shown in Fig. 9.

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